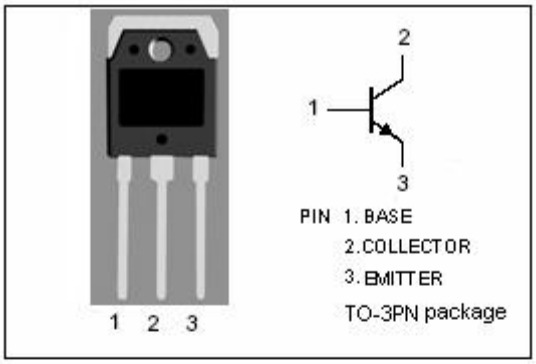
isc Silicon NPN Power Transistor — MJH16018

DESCRIPTION

- Collector-Emitter Voltage-
  : $V_{CEO(SUS)}$= 800V(Min)
- Fast Turn-Off Time
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

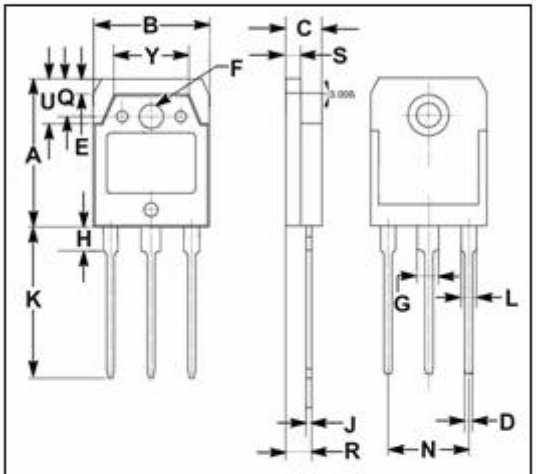
Designed for high-voltage, high-speed , power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switchmode applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	1500	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current-Continuous	8	A
I_{BM}	Base Current-Peak	12	A
P_C	Collector Power Dissipation @T_C=25℃	150	W
	Collector Power Dissipation @T_C=100℃	50	
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{(th)j-c}$	Thermal Resistance,Junction to Case	1.0	℃/W



DIM	mm MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 1mA; I_B= 0	800			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 5A ;I_B= 1A I_C= 5A ;I_B= 1A ;T_C=100℃			1.5 2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 10A ;I_B= 4A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A ;I_B= 1A I_C= 5A ;I_B= 1A ;T_C=100℃			1.5 1.5	V
I_{CBO}	Collector Cutoff Current	V_{CEV}=1500V,I_E=0 T_C=100℃			0.25 1.5	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C= 0			1.0	mA
h_{FE}	DC Current Gain	I_C= 5A ; V_{CE}= 5V	7			